

Page 10, full paragraph No. 4,

In the above-mentioned state, if the surface of the substrate 101 is etched by the impurity, molecules or atoms 103 constituting the substrate are detached or released from the substrate surface. Those molecules or atoms thus detached are monitored by using a quadrupole mass spectrometer 104. Herein, the etching start temperature T_e is a temperature at which molecules or atoms derived from the composition of the substrate start to be detected. For example, if a Si substrate is employed, the etching start temperature T_e corresponds to a temperature at which molecules or atoms derived from Si start to be detected.

IN THE CLAIMS:

Please cancel claims 6-9 without prejudice or disclaimer.

Please enter the following amended claims:

Claim 1. (Amended). A method for manufacturing a single crystal SiC on a substrate having a surface, the substrate including at least one of Si or C, the method comprising the steps of:

a first step of coating the substrate with a thin single crystal SiC layer by heating the substrate under existence of a raw material containing C or Si, or C and Si to induce surface chemical reaction between said raw material and Si or C contained in the substrate, thereby forming the thin single crystal layer; and

B3
a second step of depositing SiC on the single crystal SiC layer, which is formed in the first step, by the vapor phase growth method or the liquid phase growth method;

the first step being carried out in the manner such that the raw material is supplied in the vicinity of the surface of the substrate, and that the raw material in the vicinity of the surface of the substrate is given a partial pressure higher at least by a predetermined rate than that of an impurity, thereby suppressing the impurity from reaching the surface of the substrate and preventing the surface of the substrate from being etched by the impurity.